

Noise Analysis

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I. TRANSISTOR NOISE

A. NMOS Noise

For the NMOS with $V_{DS} = V_{GS} = 900\text{mV}$, $I_D = 439\mu\text{A}$. Additionally, $g_m = 2.44\text{mS}$ and $v^* = 440\text{mV}$ as seen in the image below.

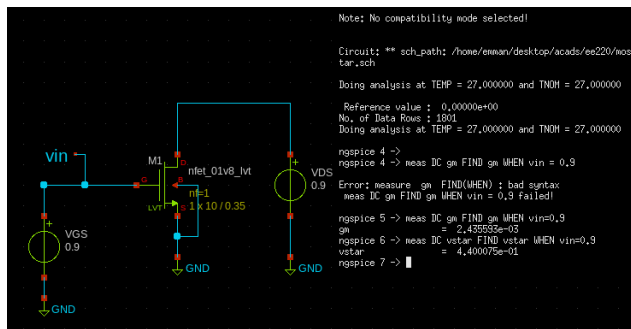


Fig. 1. g_m and v^*

The values are obtained by using the MEAS command. Note that the TT corner is used for the simulation.

B. PMOS Noise